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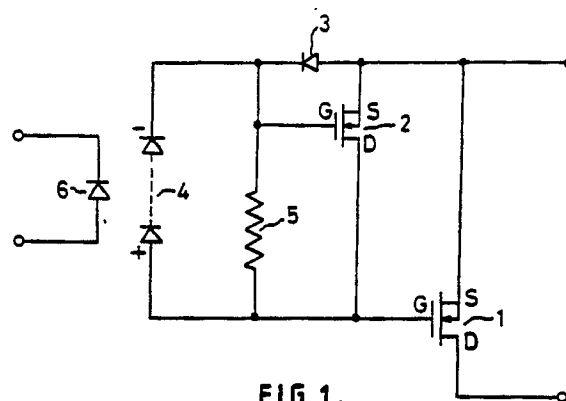
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(54) **Light-sensitive semiconductor device.**

(57) A semiconductor device is disclosed which comprises a normally-off first MOSFET (1), a normally-off second MOSFET (2) connected between the gate and source of the first MOSFET, a diode (3) connected between the gate and source of the second MOSFET (2), a resistor (5) and an optoelectric transducer array (4), both of which are connected in parallel with each other between the gate and drain of the second MOSFET (2), wherein all of the components are formed on a single semiconductor chip. Also disclosed is a semiconductor device comprising a normally-off first MOSFET, a normally-on second MOSFET connected between the gate and source of the first MOSFET, a first resistor and a diode, both of which are connected in series between the source and drain of the second MOSFET, a second resistor connected between the gate and source of the second MOSFET, an optoelectric transducer array connected between the gate of the second MOSFET and the terminal which is positioned between the first resistor and the diode, wherein all of the components are formed on a single semiconductor chip.

**FIG.1.****EP 0 371 814 A3**



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EUROPEAN SEARCH REPORT

Application Number

EP 89 31 2504

DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.5)
Y	GB-A-2 188 484 (MATSUSHITA ELECTRIC WORKS LTD) * Figure 1; page 2, line 114 - page 3, line 111 * - - -	1-6	H 03 K 17/78
Y	US-A-4 755 697 (KINZER) * Figure 1; column 4, line 61 - column 5, line 48 * - - -	1-6	
A	US-A-4 665 316 (HODGES) * Figure 2d; column 2, lines 24-37 * - - - - -	7-11	
The present search report has been drawn up for all claims			TECHNICAL FIELDS SEARCHED (Int. Cl.5)
			H 03 K
Place of search		Date of completion of search	Examiner
The Hague		14 October 90	SEGAERT P.A.O.M.P.
<div><div>CATEGORY OF CITED DOCUMENTS X: particularly relevant if taken alone Y: particularly relevant if combined with another document of the same category A: technological background O: non-written disclosure P: intermediate document T: theory or principle underlying the invention</div><div>E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons &: member of the same patent family, corresponding document</div></div>			